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Vishay Siliconix

# Automotive N-Channel 55 V (D-S) 175 °C MOSFET

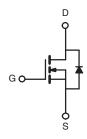


PRODUCT SUMMARY				
V <sub>DS</sub> (V)	55			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 10 V	0.020			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.026			
I <sub>D</sub> (A)	30			
Configuration	Single			

#### **FEATURES**

- TrenchFET® power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- AEC-Q101 qualified d
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





N-Channel MOSFET

ORDERING INFORMATION	
Package	DPAK (TO-252)
Lead (Pb)-free and halogen-free	SQDN30N05-20L (for detailed order number please see <a href="www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	55	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current	T <sub>C</sub> = 25 °C a	- I <sub>D</sub>	30	
	T <sub>C</sub> = 125 °C		19	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	30	Α
Pulsed Drain Current b		I <sub>DM</sub>	120	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	20	
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	20	mJ
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	50	W
	T <sub>C</sub> = 125 °C	$P_{D}$	16	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	60	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	3	C/VV

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	-				l	l	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> :	= 0 V, I <sub>D</sub> = 250 μA	55	-	-	.,
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 55 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 55 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 55 V, T <sub>J</sub> = 175 °C	-	-	250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 5 V$	$V_{DS} \ge 5 V$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.016	0.020	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.035	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.043	
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 15 A	-	0.021	0.026	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 20 A	-	34	-	S
Dynamic <sup>b</sup>	-				l	l	
Input Capacitance	C <sub>iss</sub>			-	938	1175	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	203	255	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	86	110	
Total Gate Charge <sup>c</sup>	Qg			-	12	18	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 5 V$	$V_{DS} = 25 \text{ V}, I_{D} = 35 \text{ A}$	-	4.1	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	4.8	-	
Gate Resistance	R <sub>g</sub>		f = 1 MHz	1	2.1	4.5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	7	11	
Rise Time <sup>c</sup>	t <sub>r</sub>	\ \V_DD =	$25 \text{ V, R}_{\text{I}} = 0.71 \Omega$	-	10	15	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	18	27	ns
Fall Time <sup>c</sup>	t <sub>f</sub>			-	5	8	1
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>	•					
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	120	Α
Forward Voltage	$V_{SD}$	I <sub>F</sub> = 80 A, V <sub>GS</sub> = 0 V		-	1.2	1.5	V

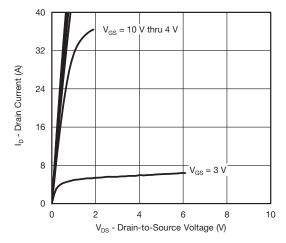
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

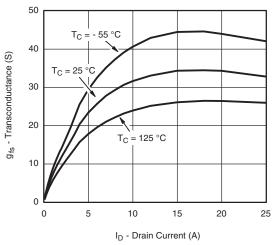
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



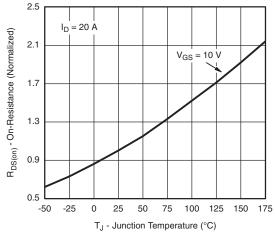
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



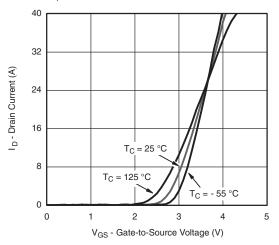
#### **Output Characteristics**



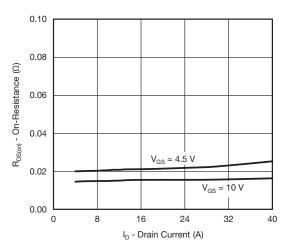
### Transconductance



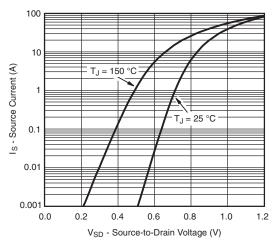
On-Resistance vs. Junction Temperature



#### **Transfer Characteristics**



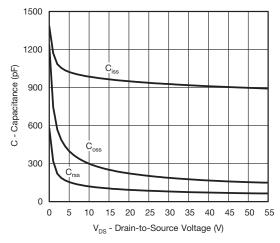
**On-Resistance vs. Drain Current** 

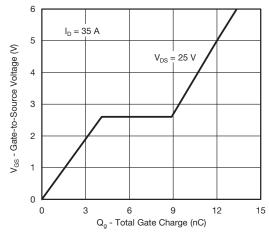


**Source Drain Diode Forward Voltage** 

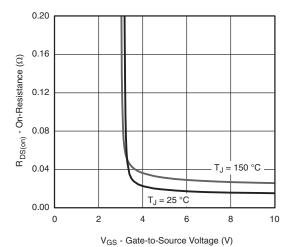


### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

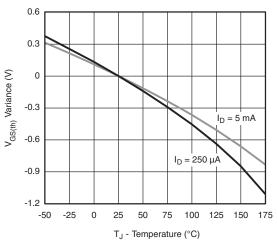




#### Capacitance

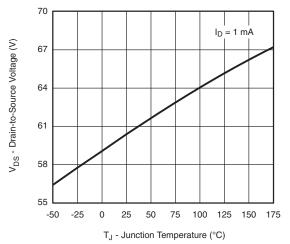


**Gate Charge** 



### On-Resistance vs. Gate-to-Source Voltage

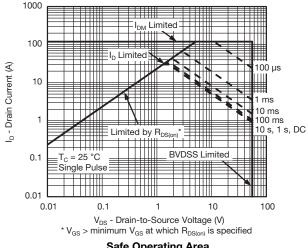
Threshold Voltage



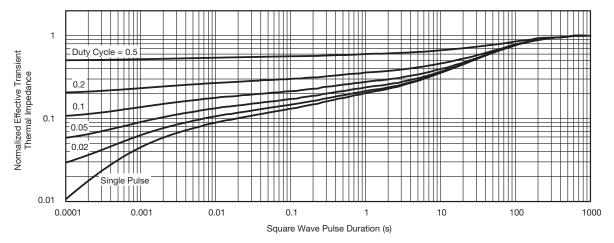
Drain Source Breakdown vs. Junction Temperature



### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



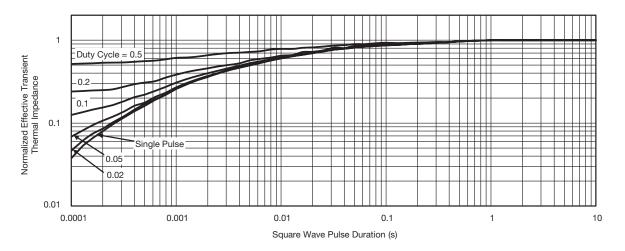
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



### Normalized Thermal Transient Impedance, Junction-to-Case

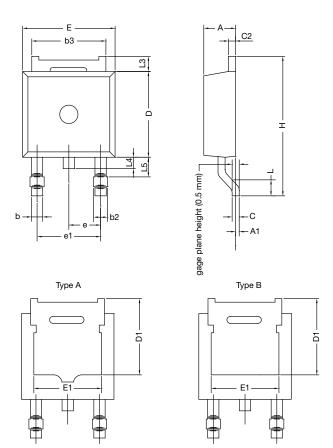
#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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## **TO-252AA Case Outline**



DIM. MILLI		METERS	INCHES	
DIIVI.	MIN.	MAX.	MIN.	MAX.
Α	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28	BSC	0.090	BSC
e1	4.56	4.56 BSC		BSC
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060

# ECN: T25-0122-Rev. C, 12-May-2025 DWG: 6019

### Notes

- Dimension L3 is for reference only
- Dimension D1 and E1 on type A and B is the same



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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